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Education Information

Doctorate, Ataturk University, Fen Bilimleri Enstitüsü, Nanoscience and Nanoengineering, Turkey 2019 - 2024

Associate Degree, Sivas Cumhuriyet University, Sağlık Hizmetleri Meslek Yüksekokulu, Optician Pr., Turkey 2022 - 2023

Associate Degree, Anadolu University, Açıköğretim Fakültesi, Computer Programming Pr., Turkey 2021 - 2023

Postgraduate, Sivas Cumhuriyet University, Fen Bilimleri Enstitüsü, Nanotechnology Engineering, Turkey 2016 - 2018

Undergraduate Double Major, Sivas Cumhuriyet University, Mühendislik Fakültesi, Mechanical Engineering, Turkey 2012 - 2016

Undergraduate, Sivas Cumhuriyet University, Mühendislik Fakültesi, Electrical-Electronics Engineering, Turkey 2011 - 2015

Foreign Languages

English, B2 Upper Intermediate

Dissertations

Doctorate, Development of Hybrid Nickel Sulfide-Based Supercapacitor Device, Ataturk University, Fen Bilimleri Enstitüsü, Nanoscience and Nanoengineering, 2024

Postgraduate, Electronic Properties of Triple GaAlAs/GaAs and GaInAs/GaAs Nano Structures, Sivas Cumhuriyet University, Fen Bilimleri Enstitüsü, Nanotechnology Engineering, 2018

Research Areas

Electrical and Electronics Engineering, Mechanical Engineering, Engineering and Technology

Academic Titles / Tasks

Research Assistant PhD, Sivas Cumhuriyet University, Mühendislik Fakültesi, Nanoteknoloji Mühendisliği, 2024 -

Published journal articles indexed by SCI, SSCI, and AHCI

- I. **Layered Transition Metal Sulfides for Supercapacitor Applications**
ÖZTÜRK O., GÜR E.
ChemElectroChem, vol.11, no.11, 2024 (SCI-Expanded)
- II. **High harmonic generations triggered by the intense laser field in GaAs/Al_xGa_{1-x}As honeycomb quantum well wires**
Alaydin B. Ö., Altun D., Öztürk O., Öztürk E.
Materials Today Physics, vol.38, 2023 (SCI-Expanded)
- III. **High harmonic generations in GaAs/AlGaAs superlattice: Effect of electric and magnetic field**
Öztürk E., Altun D., Öztürk O., Alaydin B. Ö.
Solid State Communications, vol.372, 2023 (SCI-Expanded)
- IV. **Linear and nonlinear optical properties of a superlattice with periodically increased well width under electric and magnetic fields**
ALTUN D. D., ÖZTÜRK O., ALAYDİN B. Ö., ÖZTÜRK E.
MICRO AND NANOSTRUCTURES, vol.166, 2022 (SCI-Expanded)
- V. **Intense laser field effect on the nonlinear optical properties of triple quantum wells consisting of parabolic and inverse-parabolic quantum wells**
Öztürk O., Alaydin B. Ö., Altun D., Öztürk E.
Laser Physics, vol.32, no.3, 2022 (SCI-Expanded)
- VI. **Depending on the intense laser field of the nonlinear optical rectification, second and third harmonic generation in asymmetric parabolic-step and inverse parabolic-step quantum wells**
ÖZTÜRK O., ÖZTÜRK E., Elagoz S.
PHYSICA SCRIPTA, vol.94, no.11, 2019 (SCI-Expanded)
- VII. **The effect of intense laser field on the nonlinear optical features in asymmetric multiple step and inverse V-shaped multiple step quantum wells**
Öztürk O., Öztürk E., Elagoz S.
LASER PHYSICS, vol.29, 2019 (SCI-Expanded)
- VIII. **Dependence on well widths of total optical absorption coefficient of asymmetric triple GaAlAs/GaAs and GaInAs/GaAs quantum wells**
ÖZTÜRK O., ÖZTÜRK E., Elagoz S.
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, vol.33, no.17, 2019 (SCI-Expanded)
- IX. **Nonlinear Optical Rectification, Second and Third Harmonic Generations in Square-Step and Graded-Step Quantum Wells under Intense Laser Field**
Ozturk O., Ozturk E., Elagoz S.
CHINESE PHYSICS LETTERS, vol.36, no.6, 2019 (SCI-Expanded)
- X. **Linear and nonlinear optical properties of asymmetric triple quantum wells under intense laser field**
Ozturk O., Ozturk E., Elagoz S.
LASER PHYSICS, vol.29, no.5, 2019 (SCI-Expanded)
- XI. **Linear and nonlinear optical absorption coefficient and electronic features of triple GaAlAs/GaAs and GaInAs/GaAs quantum wells depending on barrier widths**
Ozturk O., Ozturk E., Elagoz S.
OPTIK, vol.180, pp.394-405, 2019 (SCI-Expanded)
- XII. **The effect of barrier width on the electronic properties of double GaAlAs/GaAs and GaInAs/GaAs quantum wells**
Ozturk O., Ozturk E., Elagoz S.
JOURNAL OF MOLECULAR STRUCTURE, vol.1156, pp.726-732, 2018 (SCI-Expanded)

Articles Published in Other Journals

- I. **Electronic characteristics of asymmetric triple GaAlAs/GaAs and GaInAs/GaAs quantum wells depending on Al and In concentration**
ÖZTÜRK O., ÖZTÜRK E., ELAGOZ S.
Cumhuriyet Science Journal, vol.41, no.3, pp.565-570, 2020 (Peer-Reviewed Journal)
- II. **Electronic properties of double GaAlAs/GaAs and GaInAs/GaAs quantumwells as dependent on well width**
ÖZTÜRK O., ÖZTÜRK E., ELAGOZ S.
Cumhuriyet Science Journal, vol.40, no.2, pp.465-470, 2019 (Peer-Reviewed Journal)

Refereed Congress / Symposium Publications in Proceedings

- I. **Dependence on Well Widths of the Electronic Features of Triple GaAlAs/GaAs and GaInAs/GaAs Quantum Wells**
Öztürk O., Öztürk E., Elagoz S.
5th International Conference on Materials Science and Advanced-Nanotechnologies For Next Generation (MSNG-2018), Nevşehir, Turkey, 4 - 06 October 2018
- II. **Electronic characteristics of triple GaAlAs/GaAs and GaInAs/GaAs quantum wells depending on Al and In concentration**
Öztürk O., Öztürk E., Elagöz S.
5th International Conference on Materials Science and Advanced-Nanotechnologies For Next Generation (MSNG-2018) , Nevşehir, Turkey, 4 - 06 October 2018, pp.308
- III. **Second-Harmonic Generation Susceptibility in Asymmetric Triple Delta-Doped GaAs Structures**
Öztürk E., Öztürk O., Elagöz S.
5th International Conference on Materials Science and Advanced-Nanotechnologies For Next Generation (MSNG-2018) , Nevşehir, Turkey, 4 - 06 October 2018, pp.309
- IV. **Depending on Al and In concentration of the electronic properties of asymmetric double GaAlAs/GaAs and GaInAs/GaAs quantum wells**
Öztürk O., Öztürk E., Elagöz S.
4th International Conference on Engineering and Natural Sciences (ICENS-2018) , Kyiv, Ukraine, 2 - 06 May 2018, pp.630-635
- V. **The Effect of Barrier Width on the Electronic Properties of Double GaAlAs / GaAs andGaInAs / GaAs Quantum Wells**
Öztürk O., Öztürk E., Elagoz S.
MSNG 2017, Sarajevo, Bosnia And Herzegovina, 28 - 30 June 2017, pp.43

Metrics

Publication: 19

Citation (WoS): 28

Citation (Scopus): 46

H-Index (WoS): 3

H-Index (Scopus): 4